

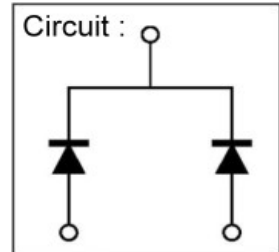
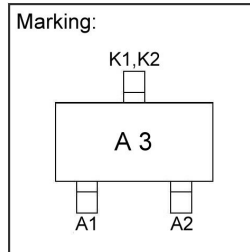
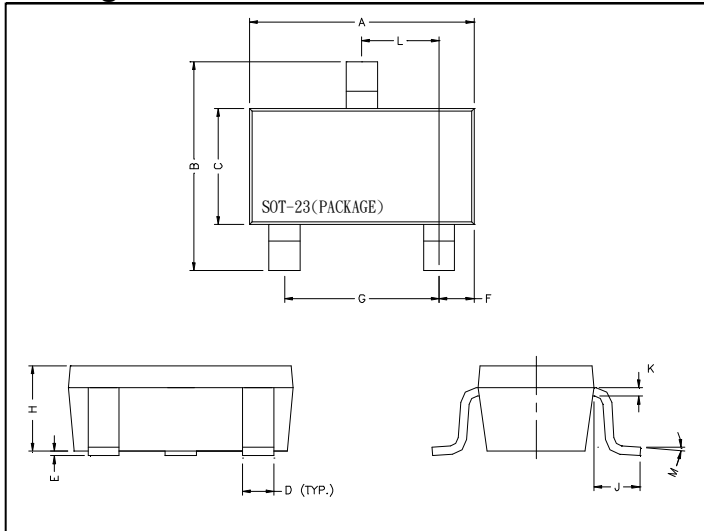
GN202K

SURFACE MOUNT, SWITCHING DIODE
VOLTAGE 80V, CURRENT 0.1A

Description

The GN202K is designed for ultra high speed switching.

Package Dimensions



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

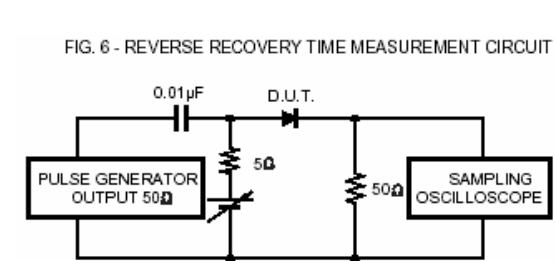
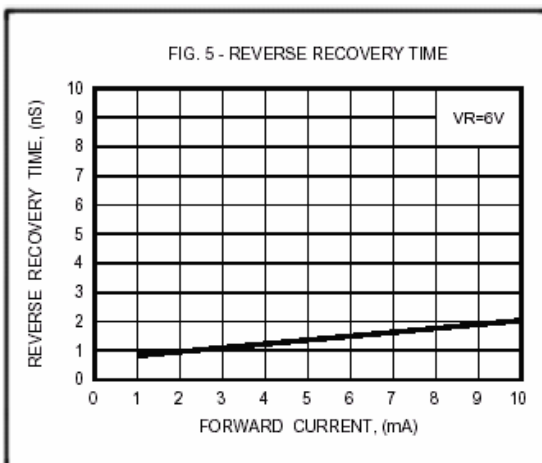
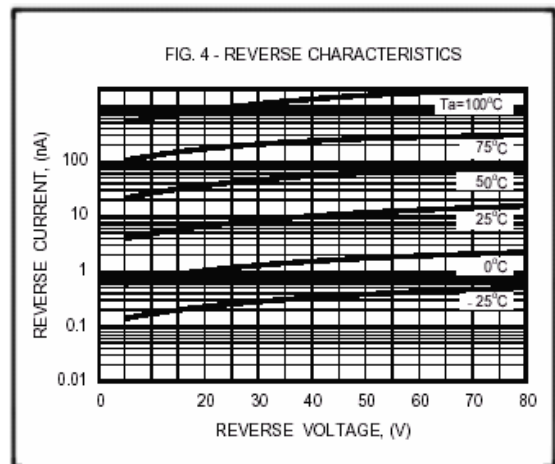
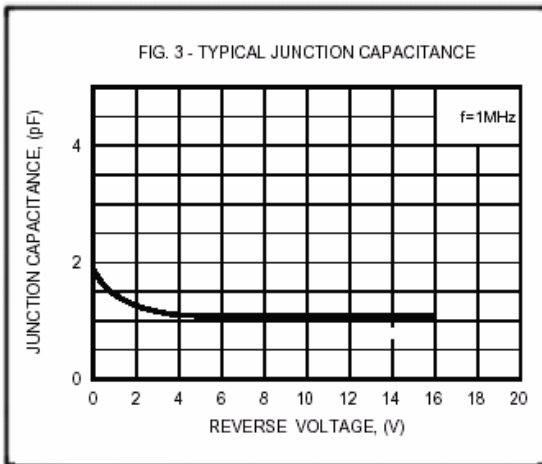
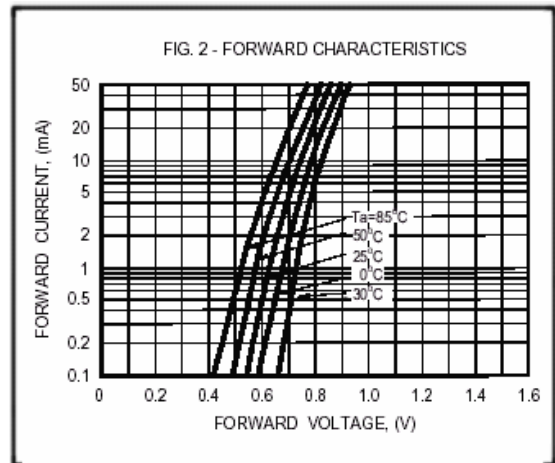
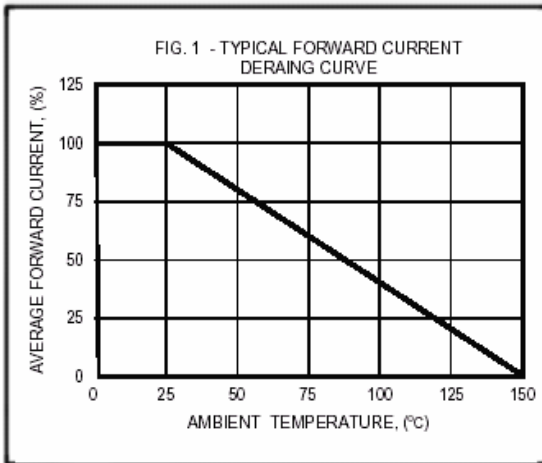
Absolute Maximum Ratings at TA = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	T _j	+150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C
Peak Reverse Voltage	V _{RM}	80	V
DC Reverse Voltage	V _R	80	V
Mean Rectifying Current	I _O	100	mA
Peak Forward Current	I _{FM}	300	mA
Peak Forward Surge Current (1uSec)	I _{FSM}	4	A
Total Power Dissipation	P _D	200	mW

Electrical Characteristics (at TA = 25°C unless otherwise noted)

Parameter	Symbol	Min.	Max.	Unit	Test Conditions
Reverse Voltage	V _R	80	-	V	I _R =100uA
Forward Voltage	V _F	-	1.2	V	I _F =100mA
Reverse Current	I _R	-	0.1	uA	V _R =70V
Capacitance between terminals	C _T	-	3.5	pF	V _R =6V, f=1MHz
Reverse Recovery Time	T _{rr}	-	4	nS	V _R =6V, I _F =5mA

Characteristics Curve



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